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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/954,864	09/17/2001	Satyadev R. Patel	P68-US	8736
26148	7590	08/18/2005	EXAMINER	
REFLECTIVITY, INC. 350 POTRERO AVENUE SUNNYVALE, CA 94085			OLSEN, ALLAN W	
			ART UNIT	PAPER NUMBER

1763

DATE MAILED: 08/18/2005

Please find below and/or attached an Office communication concerning this application or proceeding.



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Serial No. : 09954864
Applicant : Satyadev R. Patel
Filing Date : September 17, 2001
Date Mailed : August 18, 2005

ACKNOWLEDGEMENT OF REQUEST

Notice of Allowance/Allowability Mailed

The request for a copy of the initialed PTO 1449, dated March 25, 2005, has been received by the U.S. Patent and Trademark Office.

- Requested copy attached

Natarsha Horne
For the Office of Patent Publication



PTO/SB/08A (10-01)
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Substitute for form 1449A/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/854,884		
		Filing Date	8/17/01		
		First Named Inventor	Patel		
		Art Unit	1763		
		Examiner Name	Olsen, Allan		
Sheet	1	of	6	Attorney Docket Number	P68-US

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Also		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flemm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Shardwal, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
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		US- 20010002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
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		US- 20020163699	12-12-2002	Reid	
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Examiner Initials ¹	Cite No. ¹	Foreign Patent Document Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
Also		EP-0704884-A2	04-03-1996	Makita, J.		
		EP-0622582-A2	02-04-1996	Shardwal, J.K.		
		EP-0822684-A2	04-04-1996	Shardwal, J.K.		
		WO-9949508	09-30-1999	McQuarrie, A.D.		
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		EP-0878824-A3	01-19-2000	McQuarrie et al.		
		JP-1982/57088679-A	06-18-1982	Tsunetoshi, A.		
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		JP-1985/60057838-A	04-03-1985	Katsumi et al.		
Also		WO-98/32183	07-23-1998	Tai et al.		

Examiner Signature	<i>Allan Olsen</i>	Date Considered	3/7/05
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² Applicant's unique citation designation number (optional). ³ See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ⁴ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁵ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁶ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁷ Applicant is to place a check mark here if English language translation is attached.

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Substitute for form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	09/854,864	
			Filing Date	8/17/01	
			First Named Inventor	Patel	
			Art Unit	1783	
			Examiner Name	Olsen, Allan	
Sheet	2	of	8	Attorney Docket Number	P68-US

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Auo		US- 6,409,878 B1	08-25-2002	McQuarrie, et al.	
		US- 6,398,619 B1	05-28-2002	Hubers, et al.	
		US- 6,578,489 B2	08/10/03	Leung, et al.	
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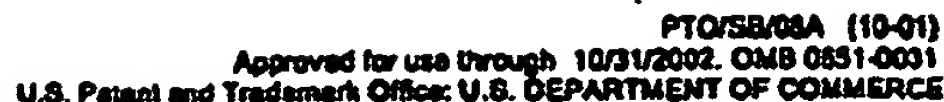
FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
Auo		JP-1987/09251981-A	09-22-1987	Kazuaki et al.		
		JP-1988/10313128-A	11-24-1988	Harmin et al.		
		JP-1988/10317169-A	12-02-1988	McQuarrie et al.		
		JP-1988/81187238-A	08-20-1988	Nobuo et al.		
		JP-1988/81270830-A	12-01-1988	Toru, T.		
		JP-1987/82071217-A	04-01-1987	Toru et al.		
		JP-1988/83155713-A	06-28-1988	Tadashi, F.		
		JP-1988/81053732-A	03-17-1988	Arata et al.		
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		JP-1988/81181131-A	08-13-1988	Shinji et al.		

Examiner Signature	<i>Allan Olsen</i>	Date Considered	3-7-05
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Substitute for form 1449-PTO

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Sheet 3 of 8

Complete if Known

Application Number	09/054,864
Filing Date	9/17/01
First Named Inventor	Patel
Art Unit	1763
Examiner Name	Olsen, Allan
Attorney Docket Number	P68-US

U.S. PATENT DOCUMENTS

[illegible]**FOREIGN PATENT DOCUMENTS**

Examiner Initials	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³	Number ⁴ - Kind Code ⁵ (if known)				
Ayo		JP	1989/01206834-A	06-22-1989	Nobuo et al.		
		JP	1989/10217921-A	08-31-1989	Tsunoo et al.		
		JP	1990/02250323-A	10-08-1990	Susumu et al.		
		JP	1991/03012921-A	01-21-1991	Nobuo et al.		
		JP	1992/04096222-A	03-27-1992	Atsuyuki, A.		
		JP	1995/07029823-A	01-31-1995	Hiroshi, T.		
A/C							

**Examiner
Signature**

Allen Ober

Date Considered

3-7-65

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Substitute for form 1449B/PTO		Complete if Known	
		Application Number	09/954,864
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Filing Date	9/17/01
		First Named Inventor	Patel
		Group Art Unit	1763
		Examiner Name	Olsen, Allan
		Attorney Docket Number	P68-US
Sheet	4	of	8

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
Auo		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F ₂ and XeF ₂ Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
		GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
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Examiner Signature	Allan Olsen	Date Considered	3-7-05
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	8/17/01
		First Named Inventor	Patel
		Group Art Unit	1763
		Examiner Name	Olsen, Allan
		Attorney Docket Number	P68-US
Sheet	6	of	6

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
Auo		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/K ₂ F ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metals", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF ₂ Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Microelectronics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
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Auo		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed XeF ₂ Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

Examiner Signature	<i>Allan Olsen</i>	Date Considered	3-7-05
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